

ABSTRACT OF THE DISCLOSURE

A gate insulating film made of silicon oxynitride is disposed on the partial surface area of a semiconductor substrate. A gate electrode is disposed on the gate insulating film. Source and drain regions are disposed on both sides
5 of the gate electrode. An existence ratio of subject nitrogen atoms to a total number of nitrogen atoms in the gate insulating film is 20 % or smaller, wherein three bonds of each subject nitrogen atom are all coupled to silicon atoms and remaining three bonds of each of three silicon atoms connected to the subject nitrogen atom are all coupled to other nitrogen atoms.

10